Abstracts

InGaP PHEMTs for wireless power applications

E. Lan, B. Pitts, M. Mikhov and O. Hartin. "InGaP PHEMTs for wireless power applications." 2001 MTT-S International Microwave Symposium Digest 01.3 (2001 Vol. III [MWSYM]): 2155-2157 vol.3.

This paper shows that we have successfully fabricated a InGaP PHEMT device with a tight threshold voltage distribution of 22 mV by using InGaP as barrier layer material. Fabricated device performance is similar to our standard AlGaAs PHEMT for low voltage operation. A 15 mm device delivers 30 dBm output power, 10.2 dB associated gain, and 67% power added efficiency at 1 dB compression point while operated at 3.5 V and 1.9 GHz.

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